

## CLAIMS

What is claimed is:

1. An electro-optic device comprising:
  - a pair of substrates;
  - an electro-optic material disposed between the substrates; and
  - means for applying an electric field to the electro-optic material;
  - a material enclosure region in which the electro-optic material is enclosed;
  - reflection electrodes provided on one of the pair of substrates in the material enclosure region, the reflection electrodes having a multilayer structure including :
    - a reflective conductive layer made of one of silver and a silver alloy;
  - and
    - a transparent conductive layer provided on the reflective conductive layer; and
    - external wirings connected to the reflection electrodes and provided outside the material enclosure region, the external wirings having a transparent conductive layer equivalent to that of the multilayer structure;
  - wherein the transparent conductive layer of the reflection electrodes has a thickness larger than that of the reflective conductive layer.
2. The electro-optic device of Claim 1, wherein the reflective conductive layer has a thickness of 80 nm to 300 nm.

3. The electro-optic device of Claim 1, further comprising an underlying insulating layer between said one of the pair of substrates and said reflective conductive layers.

4. A method for manufacturing an electro-optic device having a pair of substrates, an electro-optic material provided between the substrates, and means for applying an electric field to the electro-optic material, the method comprising:

a step of selectively forming reflective conductive layers made of one of silver and a silver alloy on one of the pair of substrates only in a first region to be used as a material enclosure region in which the electro-optic material is enclosed; and

a step of forming transparent conductive layers in the first region and a second region located outside the material enclosure region, the transparent conductive layers having a thickness larger than that of the reflective conductive layers.

5. The method for manufacturing an electro-optic device of Claim 4, wherein the reflective conductive layers are formed to have a thickness of 80 nm to 300 nm.

6. The method for manufacturing an electro-optic device of Claim 4, further comprising a step of forming an underlying insulating layer between said one of the pair of substrates and the reflective conductive layers.

7. An electronic apparatus comprising:

the electro-optic device according to Claim 1; and  
control means for controlling the electro-optic device.